

(19)
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(22)	2002 10 29	
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(74)		
:		
(54)		

Ox SiNx , 가 (outgasing) Si

2f

1 2a 2f

*

20 : 21 :

22 : 1 23 : 2

24 : 3 25 :

26 : (buffer layer) 27 :

28 :

SiOx SiNx , 가 (outgasing)

가 (' EL ') , ,

1 EL .

EL (glass) (film) (10)

ITO(Indium Tin Oxide) (11) (12) , (13)

(12) ,

(11), (12), (13) (14) , ,

(15) , (15) 가 , (14)

EL , , (photoresist)

(polyimide) , (Joule) (carbonizin

g) (short) ,

가

SiOx SiNx ,

2a , (20) (stripe)

(21) , (glass)

(21) (27) (21) (28) (26) (26)

(21) (26) (26) (21)

(27) (28)

가

2

(28) 100 ~ 10,000

100 ~ 2,000 가

(28) (25) (Plasma Enhanced Chemical Vapor Deposition ; PEC

VD) SUS

(27) (28) SUS

(Encapsulation) 가

EL

SiOx , SiNx

가

가

(57)

1.

;

(etching rate) 1 2 3

3 1

;

(buffer layer) ;

2.

1 ;

(etching rate) 2 가 , 1 가 ,

3.

1 2 ,

1 2 ;

SiOx(x = 1, 2, 3...) ,

3 ;

SiNx(x = 1, 2, 3...) , .

4.

3 ,

1 3 ;

가 200nm ~ 500nm ,

2 ;

가 2 μ m ~ 5 μ m , .

5.

1 , (buffer layer) ;

SiOx, SiO₂, SiOxNy, Si₃N₄, SiNx , .

6.

1 5 , (buffer layer) ;

가 500 μ m ~ 3,000 μ m , .

7.

1 ;

1 (etching rate) 1 , 2 ,

3 2 ;

2 3 (contact hole)

1 3 ;

3 1 (buffer layer)

4 ;

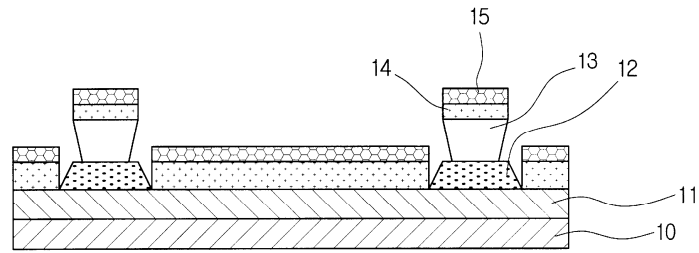
4 5 , .

8.

7 , ;

(etching rate) 2 가 , 1 가 , .

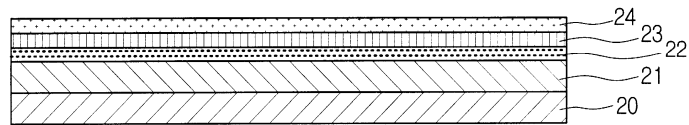
1



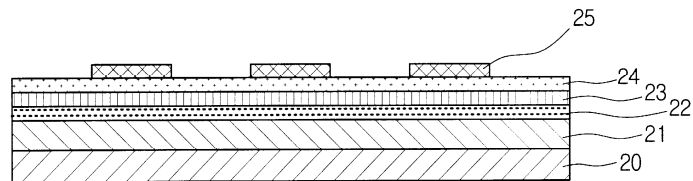
2a



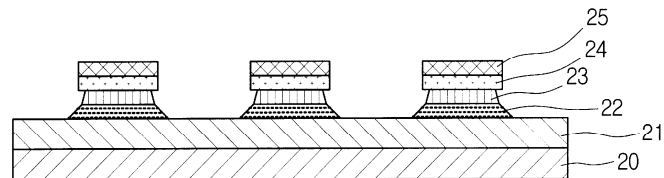
2b



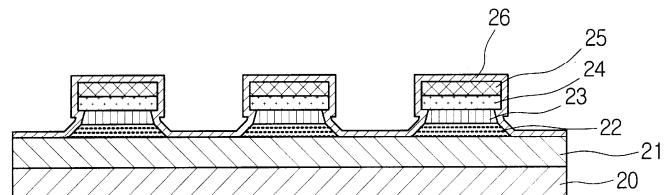
2c



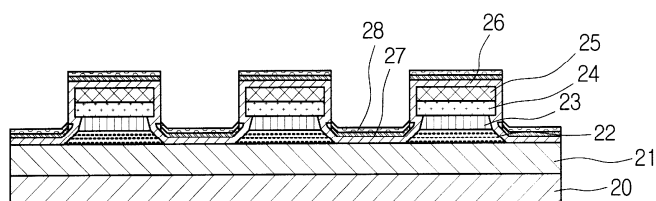
2d



2e



2f



专利名称(译)	有机电致发光显示装置及其制造方法		
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外部链接	Espacenet		

摘要(译)

对于本发明的有机电致发光显示装置，旨在提高装置的发光效率，当有机化合物隔板中的无机材料如SiO_x代替有机化合物如隔板材料时光刻胶兰花马来酰亚胺和使用SiN_x，通过代替使用无机材料的超薄膜缓冲层，绝缘层，使由于产生的放气（脱气）导致的器件寿命减少最小化。有机，电场，辐射，显示器，无机材料，隔墙，绝缘层，超薄膜。

